

NUP1301U Ultra low capacitance ESD protection array Rev. 1 – 28 January 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Ultra low capacitance ElectroStatic Discharge (ESD) protection array in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package designed to protect one signal line in rail-to-rail configuration from the damage caused by ESD and other transients.

### **1.2 Features and benefits**

- ESD protection of one signal line (rail-to-rail configuration)
- Ultra low diode capacitance: C<sub>d</sub> = 0.6 pF
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); I<sub>PP</sub> = 11 A
- AEC-Q101 qualified

### **1.3 Applications**

- Telecommunication networks
- Video line protection
- Microcontroller protection
- I<sup>2</sup>C-bus protection
- Antenna power supply
- Analog audio
- Class-D amplifier

### 1.4 Quick reference data

#### Table 1. Quick reference data

 $T_{amb} = 25 \ ^{\circ}C \ unless \ otherwise \ specified.$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	80	V
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V	-	0.6	0.75	pF
I <sub>R</sub>	reverse current	V <sub>R</sub> = 80 V	-	-	100	nA



#### Ultra low capacitance ESD protection array

## 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND	ground		
2	V <sub>CC</sub>	supply voltage		3
3	I/O	input/output	1 2	

## 3. Ordering information

Table 3. Ordering information					
Type number	Packag	e			
	Name	Description	Version		
NUP1301U	-	plastic surface-mounted package; 3 leads	SOT323		

## 4. Marking

Table 4. Marking	
Type number	Marking code <sup>[1]</sup>
NUP1301U	*VU

[1] \* = placeholder for manufacturing site code

## 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V <sub>RRM</sub>	repetitive peak reverse voltage		-	80	V
V <sub>R</sub>	reverse voltage		-	80	V
I <sub>F</sub>	forward current		<u>[1]</u> _	215	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.25$	-	500	mA
I <sub>FSM</sub>	non-repetitive peak	square wave	[2]		
	forward current	t <sub>p</sub> = 1 μs	-	4	А
		t <sub>p</sub> = 1 ms	-	1	А
		t <sub>p</sub> = 1 s	-	0.5	А

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Symbol	Parameter	Conditions	Min	Max	Unit
Per devic	e				
P <sub>PP</sub>	peak pulse power	t <sub>p</sub> = 8/20 μs	[3][4] _	220	W
I <sub>PP</sub>	peak pulse current	t <sub>p</sub> = 8/20 μs	<u>[3][4]</u>	11	А
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[5][6]</u>	200	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

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[2]  $T_j = 25 \circ C$  prior to surge.

[3] Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

[4] Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

- [5] Single diode loaded.
- [6] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### Table 6. ESD maximum ratings

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>ESD</sub>	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	<u>[1][2]</u>	-	30	kV
		machine model		-	400	V
		MIL-STD-883 (human body model)		-	10	kV

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

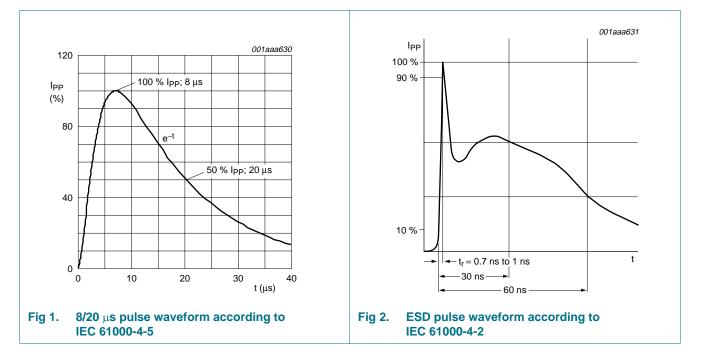
#### Table 7. ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3B (human body model)	> 8 kV

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## 6. Thermal characteristics

Table 8.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per devie	ce						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1][2]</u>	-	-	625	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	300	K/W

[1] Single diode loaded.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### Ultra low capacitance ESD protection array

## 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	9					
V <sub>BR</sub>	breakdown voltage	I <sub>R</sub> = 100 μA	100	-	-	V
V <sub>F</sub>	forward voltage		<u>[1]</u>			
	I <sub>F</sub> = 1 mA	-	-	715	mV	
		I <sub>F</sub> = 10 mA	-	-	855	mV
		I <sub>F</sub> = 50 mA	-	-	1	V
		I <sub>F</sub> = 150 mA	-	-	1.25	V
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 25 V	-	-	30	nA
		V <sub>R</sub> = 80 V	-	-	100	nA
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	25	μA
		V <sub>R</sub> = 80 V; T <sub>j</sub> = 150 °C	-	-	35	μA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0 V	-	0.6	0.75	pF
Per devic	e					
V <sub>CL</sub>	clamping voltage	I <sub>PP</sub> = 1 A	[2][3]	-	3	V
		I <sub>PP</sub> = 11 A	[2][3]	-	20	V

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .

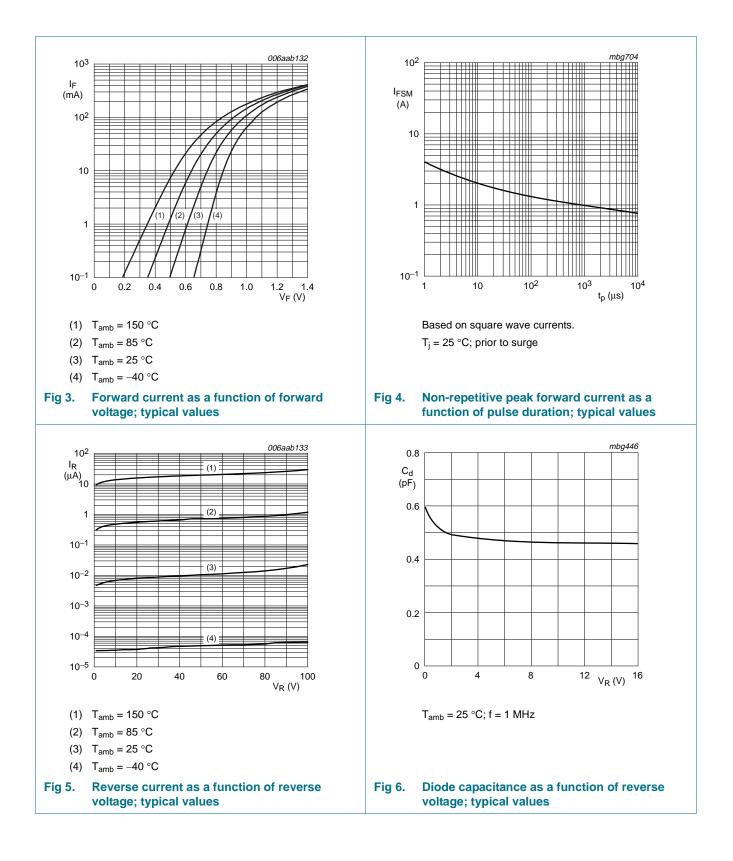
[2] Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

[3] Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

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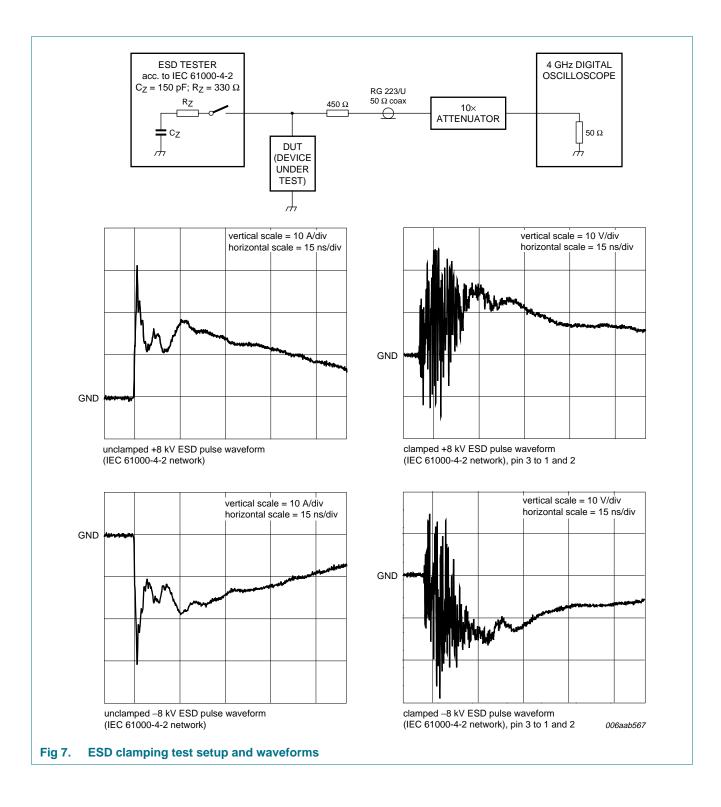
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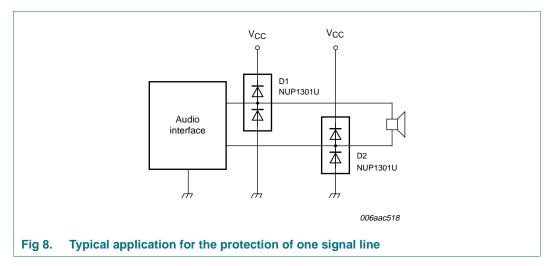
#### Ultra low capacitance ESD protection array



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## 8. Application information

Protection of a single (high-speed) data line in rail-to-rail configuration. The protected data line is connected to pin 3. Pin 1 is connected to ground (GND) and pin 2 is connected to the supply rail (supply voltage  $V_{CC}$ ). When the transient voltage exceeds the forward voltage drop of one diode, the transient is directed either to the supply rail or to GND. The advantages of these solutions are: low line capacitance (0.6 pF typically), fast response time, and low clamping voltage.



#### Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the NUP1301U as close to the input terminal or connector as possible.
- 2. The path length between the NUP1301U and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

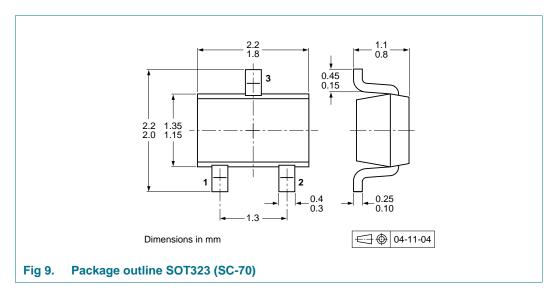
## 9. Test information

### 9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### Ultra low capacitance ESD protection array

## **10. Package outline**



## **11. Packing information**

#### Table 10. Packing methods

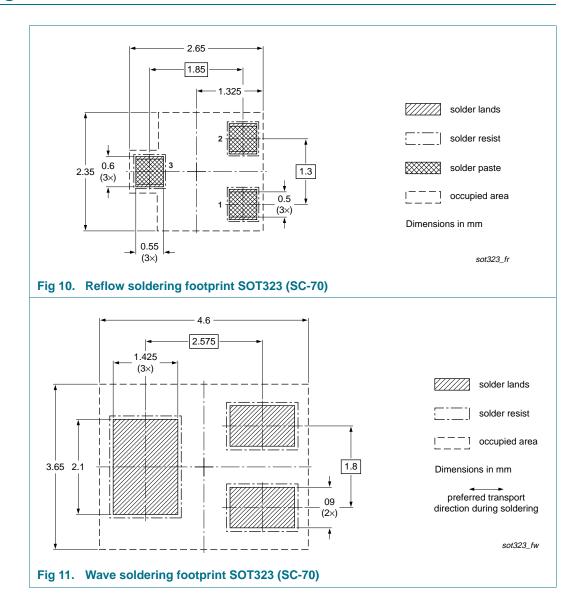
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	e Description Packing q		j quantity	
			3000	10000	
NUP1301U	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135	

[1] For further information and the availability of packing methods, see <u>Section 15</u>.

### Ultra low capacitance ESD protection array

## 12. Soldering



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## 13. Revision history

Table 11. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
NUP1301U v.1	20110128	Product data sheet	-	-

#### Ultra low capacitance ESD protection array

## 14. Legal information

### 14.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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